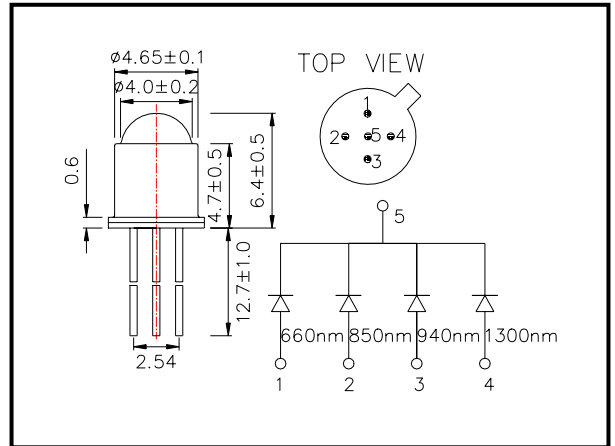


L660/850/940/1300-35B32

L660/850/940/1300-B32 consists of an AlGaAs'(660, 850nm), GaAs'(940nm) and InGaAs'(1300nm) LED mounted on TO-18 stem with a spherical glass lens. LED are connected as cathode common

multi-wavelength LED

◆Outer dimension(Unit: mm)



◆ Specifications

- | | |
|---------------------|-------------------------|
| 1) Product Name | Multi-wavelength LED |
| 2) Type No. | L660/850/940/1300-35B32 |
| 3) Chip | |
| (1) Chip material | GaAs, AlGaAs, InGaAs |
| (2) Peak wavelength | 660, 850, 940, 1300nm |
| 4) Package | |
| (1) Stem | TO-18 5pin type |
| (2) Pins Connection | Cathode Common |
| (3) Lens | Φ5mm spherical glass |

◆ Absolute Maximum Ratings/ per each one chip [Ta=25°C]

Item	Symbol	Maximum Rated Value				Unit
		660	850	940	1300	
Power Dissipation	Pd	120	160	140	120	mW
Forward Current	IF	50	100	100	100	mA
Pulse Forward Current	IF	200	1000	1000	1000	mA
Reverse Voltage	VR	5				V
Operating Temperature	TOPR	-20 ~ +80				°C
Storage Temperature	TSTG	-30 ~ +100				°C
Soldering Temperature	TSOL	240				°C

‡Soldering condition: Soldering condition must be completed within 3 seconds at 240°C and is allowed in the area apart 3mm from the bottom of the lamp.

◆ Electro-Optical Characteristics/ per each one chip [Ta=25°C]

Symbol	Wavelength	Condition	Minimum	Typical	Maximum	Unit
VF	660	IF=20mA		1.9	2.3	V
	850			1.4	1.6	
	940			1.2	1.4	
	1300			0.8	1.3	
IR		VR=5V			10	uA
PO	660	IF=20mA		1.4		mW
	850			5.0		
	940			2.5		
	1300			1.0		
λP	660	IF=20mA	645	655	665	nm
	850		840	850	860	
	940		935	940	955	
	1300		1250	1300	1350	
Δλ	660	IF=20mA		20		nm
	850			30		
	940			45		
	1300			75		

‡Total Radiated Power is measured by Photodyne #500

‡Radiated Power of 1300nm is measured by Ando Optical Multi Meter AQ2140 & AQ2742